

# Hiroaki Hanafusa

## List of Publications by Year in descending order

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docs citations

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Investigation on electrical characteristics of TFTs fabricated with germanium films crystallized by atmospheric-pressure micro thermal plasma jet irradiation. Japanese Journal of Applied Physics, 2022, 61, SC1011.	1.5	4
2	Direct observation of three-dimensional transient temperature distribution in SiC Schottky barrier diode under operation by optical-interference contactless thermometry imaging. Applied Physics Express, 2022, 15, 026502.	2.4	2
3	Direct observation of ultra-rapid solid phase crystallization of amorphous silicon films irradiated by micro-thermal-plasma-jet. Materials Science in Semiconductor Processing, 2021, 121, 105357.	4.0	3
4	Investigation on characteristics of millisecond solid-phase crystallized silicon films annealed by atmospheric pressure DC arc discharge micro-thermal-plasma-jet and their application to bottom-gate thin film transistors fabrication. Japanese Journal of Applied Physics, 2021, 60, 105502.	1.5	0
5	Development of high-yield layer transfer process of single-crystalline silicon thin films on plastic substrate and its application to multi-functional device integration. Japanese Journal of Applied Physics, 2020, 59, SGGJ02.	1.5	0
6	Band-energy estimation on silicon cap annealed 4H-SiC surface using hard X-ray photoelectron spectroscopy. Surface Science, 2020, 696, 121592.	1.9	0
7	In situ monitoring to visualize temperature distribution in molten silicon region formed under atmospheric pressure thermal plasma jet irradiation. Applied Physics Express, 2020, 13, 015507.	2.4	2
8	Precise measurement of the temperature of a silicon wafer by an optical-interference contactless thermometer during rapid plasma processing. Journal of Applied Physics, 2020, 127, .	2.5	6
9	Large area annealing by magnetic field scanning of atmospheric pressure thermal plasma beam. Japanese Journal of Applied Physics, 2020, 59, SJJF01.	1.5	0
10	Single-Crystalline Si-CMOS Circuit Fabrication on Polyethylene Terephthalate Substrate by Meniscus Force-Mediated Layer Transfer. IEEE Journal of the Electron Devices Society, 2019, 7, 943-948.	2.1	1
11	Extremely high-power-density atmospheric-pressure thermal plasma jet generated by the nitrogen-boosted effect. Japanese Journal of Applied Physics, 2018, 57, 06JH01.	1.5	3
12	Generation of ultra high-power thermal plasma jet and its application to crystallization of amorphous silicon films. Japanese Journal of Applied Physics, 2017, 56, 06HE05.	1.5	4
13	High-temperature and high-speed oxidation of 4H-SiC by atmospheric pressure thermal plasma jet. Japanese Journal of Applied Physics, 2017, 56, 040304.	1.5	8
14	High Efficiency Activation of Phosphorus Atoms in 4H-SiC by Atmospheric Pressure Thermal Plasma Jet Annealing. Materials Science Forum, 2016, 858, 535-539.	0.3	4
15	High-efficiency impurity activation by precise control of cooling rate during atmospheric pressure thermal plasma jet annealing of 4H-SiC wafer. Japanese Journal of Applied Physics, 2015, 54, 06GC01.	1.5	5
16	Ge Flat Layer Growth on Heavily Phosphorus-Doped Si(001) by Sputter Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 055502.	1.5	3
17	Direct observation of grain growth from molten silicon formed by micro-thermal-plasma-jet irradiation. Applied Physics Letters, 2012, 101, 172111.	3.3	16
18	SiGe Sputter Epitaxy Technique and Its Application to SiGe Devices. Procedia Engineering, 2012, 36, 396-403.	1.2	2

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19	Ge Flat Layer Growth on Heavily Phosphorus-Doped Si(001) by Sputter Epitaxy. Japanese Journal of Applied Physics, 2012, 51, 055502.	1.5	8
20	Si/Ge Hole-Tunneling Double-Barrier Resonant Tunneling Diodes Formed on Sputtered Flat Ge Layers. Applied Physics Express, 2011, 4, 024102.	2.4	13
21	Strain Distribution Analysis of Sputter-Formed Strained Si by Tip-Enhanced Raman Spectroscopy. Applied Physics Express, 2011, 4, 025701.	2.4	19
22	Strain-Relaxed Si <sub>1-x</sub> Ge <sub>x</sub> and Strained Si Grown by Sputter Epitaxy. Japanese Journal of Applied Physics, 2008, 47, 3020.	1.5	22
23	Properties of Al Ohmic Contacts to n-type 4H-SiC Employing a Phosphorus-Doped and Crystallized Amorphous-Silicon Interlayer. Materials Science Forum, 0, 778-780, 649-652.	0.3	5
24	Estimation of Phosphorus-Implanted 4H-SiC Layer Recrystallization by Electron-Back-Scattering Diffraction Pattern Analysis. Materials Science Forum, 0, 821-823, 391-394.	0.3	1
25	Growth of high-crystallinity silicon films by a combination of intermittent pulse heating and plasma-enhanced chemical vapor deposition. Japanese Journal of Applied Physics, 0, , .	1.5	0